

Silicon PNP Power Transistors

2SA959

DESCRIPTION

- With TO-3 package
- Excellent safe operating area

APPLICATIONS

- For high power audio ,stepping motor and other linear applications
- Relay or solenoid drivers
- DC-DC converters inverters

PINNING(see Fig.2)

PIN	DESCRIPTION
1	Base
2	Emitter
3	Collector

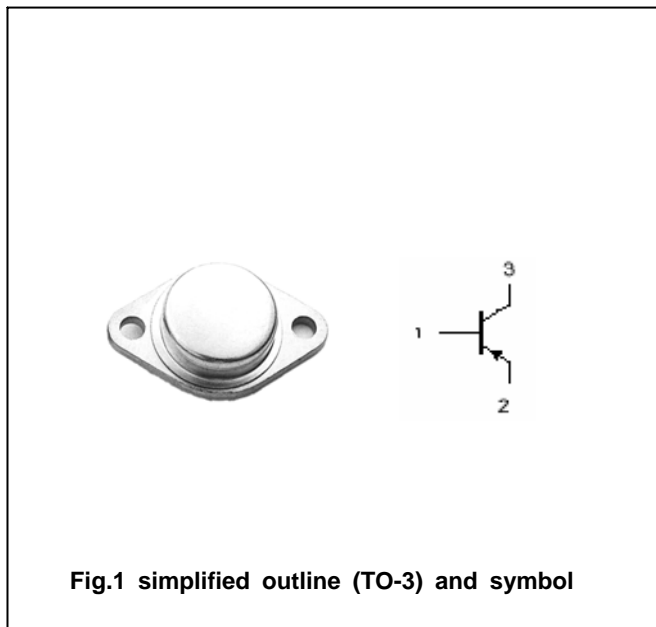


Fig.1 simplified outline (TO-3) and symbol

Absolute maximum ratings(Ta=°C)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V _{CBO}	Collector-base voltage	Open emitter	-100	V
V _{CEO}	Collector-emitter voltage	Open base	-100	V
V _{EBO}	Emitter-base voltage	Open collector	-7	V
I _C	Collector current		-10	A
P _C	Collector power dissipation	T _C =25°C	100	W
T _j	Junction temperature		150	°C
T _{stg}	Storage temperature		-65~200	°C

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
R _{th j-c}	Thermal resistance junction to case	0.98	°C/W

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CHARACTERISTICS

T_j=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{(BR)CEO}	Collector-emitter breakdown voltage	I _C =-50mA ; I _B =0	-100			V
V _{(BR)CBO}	Collector-base breakdown voltage	I _C =-1m A ; I _E =0				
V _{(BR)EBO}	Emitter-base breakdown voltage	I _E =-1mA ; I _C =0				
V _{CEsat}	Collector-emitter saturation voltage	I _C =-5A; I _B =-0.5A			-2.0	V
V _{BEsat}	Base-emitter saturation voltage	I _C =-5A; I _B =-0.5A			-2.5	V
I _{CBO}	Collector cut-off current	V _{CB} =-100V; I _E =0			-0.1	mA
I _{EBO}	Emitter cut-off current	V _{EB} =-7V; I _C =0			-0.1	mA
h _{FE}	DC current gain	I _C =-5A ; V _{CE} =-5V	30		200	

PACKAGE OUTLINE

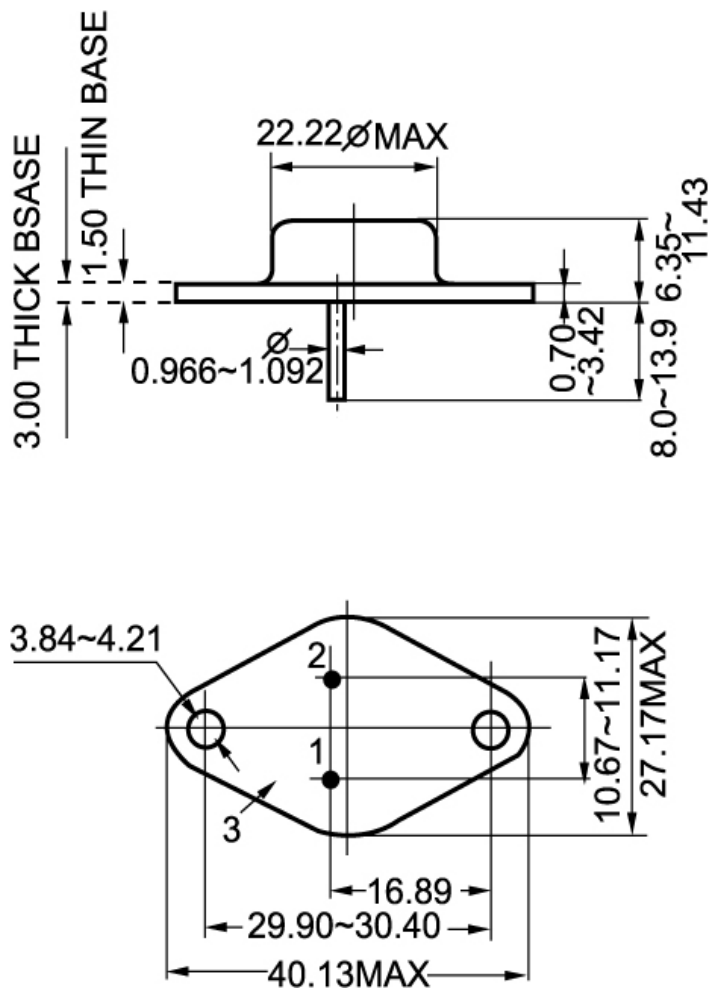


Fig.2 outline dimensions (unindicated tolerance: ±0.1mm)